

## Notice of References Cited

Application/Control No.	Applicant(s)/	Patent Under	
09/772,858	Reexamination KAMIJIMA, AKIFUMI		
Examiner	Art Unit		
Allan W. Olsen	1763	Page 1 of 1	

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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)

Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.